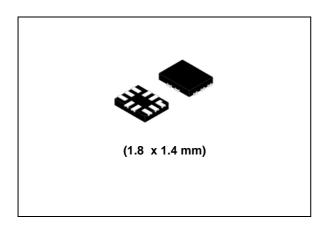
AS21P2TLR



Low voltage 0.5 Ω max dual single-pole double-throw analog switch with break-before-make

Datasheet - production data



Features

- Ultra low power dissipation: I_{CC} = 0.2 μA (max.) at T_A = 85 °C
- Low ON resistance V_{IN} = 0 V:
 - R_{ON} = 0.50 Ω (max. T_A = 25 °C) at V_{CC} = 4.3 V
 - R_{ON} = 0.50 Ω (max. T_A = 25 °C) at V_{CC} = 3.6 V
- Wide operating voltage range:
 V_{CC} (OPR) = 1.65 to 4.3 V single supply
- 4.3 V tolerant and 1.8 V compatible threshold on digital control input at V_{CC} = 2.3 to 4.3 V
- Latch-up performance exceeds 300 mA (JESD 17)
- ESD performance: HMB > 2 kV (MIL STD 883 method 3015)

Description

The AS21P2TLR is a high-speed CMOS single-pole double-throw (SPDT) analog switch or dual 2:1 multiplexer/demultiplexer bus switch fabricated using silicon gate C²MOS technology. Designed to operate from 1.65 to 4.3 V, this device is ideal for portable applications.

It offers very low ON resistance (R_{ON} < 0.5 Ω) at V_{CC} = 3.6 V. The nIN inputs are provided to control the independent channel switches nS1 and nS2. The switches nS1 are ON (connected to common ports Dn) when the nIN input is held high and OFF (state of high impedance exists between the two ports) when nIN is held low. The switches nS2 are ON (connected to common ports Dn) when the nIN input is held low and OFF (state of high impedance exists between the two ports) when IN is held high. Additional key features are fast switching speed, break-before-make delay time and ultralow power consumption. All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD and excess transient voltage immunity.

Table 1. Device summary

Order code	Package	Packing
AS21P2TLRQ	QFN10L (1.8 x 1.4 mm)	Tape and reel

Contents AS21P2TLR

Contents

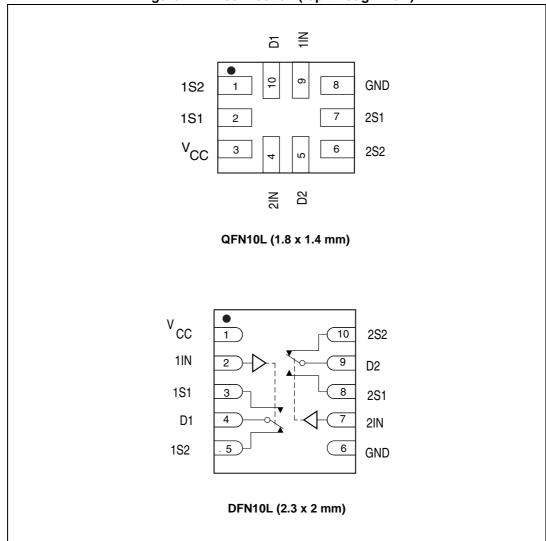
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AS21P2TLR Pin settings

1 Pin settings

1.1 Pin connection

Figure 1. Pin connection (top through view)



Pin settings AS21P2TLR

1.2 Pin description

Table 2. Pin description

Pin number	Symbol	Name and function
1	1S2	Independent channel
2	1S1	Independent channel
3	V _{CC}	Positive voltage supply
4	2IN	Control
5	D2	Common channel
6	2S2	Independent channel
7	2S1	Independent channel
8	GND	Ground (0 V)
9	1IN	Control
10	D1	Common channel

Note: Exposed pad must be soldered to a floating plane. Do NOT connect to power or ground.

2 Input equivalent circuit and truth table

Figure 2. Input equivalent circuit

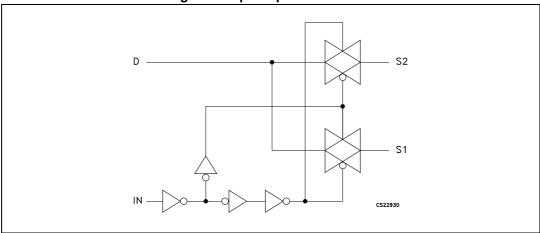


Table 3. Truth table

IN	Switch S1	Switch S2
Н	ON	OFF ⁽¹⁾
L	OFF ⁽¹⁾	ON

1. High impedance.

Maximum rating AS21P2TLR

3 Maximum rating

Stressing the device above the rating listed in the "Absolute maximum ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	-0.5 to 5.5	V
VI	DC input voltage	-0.5 to V _{CC} + 0.5	V
V _{IC}	DC control input voltage	-0.5 to 5.5	V
Vo	DC output voltage	-0.5 to V _{CC} + 0.5	V
I _{IKC}	DC input diode current on control pin (V _{IN} < 0 V)	-50	mA
I _{IK}	DC Input diode current (V _{IN} < 0 V)	±50	mA
I _{OK}	DC output diode current	±20	mA
I _O	DC output current	±300	mA
I _{OP}	DC output current peak (pulse at 1 ms, 10% duty cycle)	±500	mA
I _{CC} or I _{GND}	DC V _{CC} or ground current	±100	mA
P_{D}	Power dissipation at T _A = 70 °C	1120	mW
T _{STG}	Storage temperature	-65 to 150	°C
T _L	Lead temperature (10 sec)	300	°C

Table 5. Recommended operating conditions

Symbol	Paramete	er	Value	Unit
V _{CC}	Supply voltage		1.65 to 4.3	V
V _I	Input voltage		0 to V _{CC}	V
V _{IC}	Control input voltage		0 to 4.3	V
V _O	Output voltage		0 to V _{CC}	V
T _{op}	Operating temperature		-40 to 85	°C
dt/dv	Input rise and fall time control	V _{CC} = 1.65 to 2.7 V	0 to 20	ns/V
di/dv	input	V _{CC} = 3.0 to 4.3 V	0 to 10	113/ V

4 Electrical characteristics

Table 6. DC specifications

						Value			
Symbol	Parameter	V _{CC} (V)	Test condition	T _A =	= 25 °C	;	-40 to 8	5 °C	Unit
				Min	Тур	Max	Min	Max	
		1.65 – 1.95		0.65 V _{CC}			0.65 V _{CC}		
		2.3 – 2.5		1.2			1.2		
V_{IH}	High level input voltage	2.7 – 3.0		1.3			1.3		٧
		3.0 – 3.6		1.4			1.4		
		4.3		1.5			1.5		
		1.65 – 1.95				0.25		0.25	
		2.3 – 2.5				0.25		0.25	
V_{IL}	Low level input voltage	2.7 – 3.0				0.25		0.25	V
		3.0 – 3.6				0.30		0.30	
		4.3				0.40		0.40	
		4.3	$V_S = 0 \text{ V to } V_{CC}$ $I_S = 100 \text{ mA}$		0.45	0.50		0.60	Ω
	Switch ON resistance	3.6			0.45	0.50		0.60	
R _{ON}		3.0			0.50	0.55		0.60	
		2.3	15 100 11,11		0.60	0.70		0.80	
		1.8			0.80	0.9		1.0	
ΔR _{ON}	ON resistance match between channels ⁽¹⁾ , ⁽²⁾	2.7	V _S = 1.5 V I _S = 100 mA		0.1				Ω
		4.3			0.15	0.20		0.20	
		3.6			0.15	0.20		0.20	
Б	ON resistance	3.0	V _S = 1.5 V		0.15	0.20		0.20	
R _{FLAT}	flatness (3)	2.7	I _S = 100 mA		0.15	0.20		0.20	Ω
		2.3			0.20	0.25		0.25	
		1.65			0.35	0.45		0.45	
I _{OFF}	OFF state leakage current (nSn), (Dn)	4.3	V _S = 0.3 or 4 V			±20		±100	nA
I _{IN}	Input leakage current	0 – 4.3	V _{IN} = 0 to 4.3 V			±0.05		±1	μА
I _{CC}	Quiescent supply current ⁽¹⁾	1.65 – 4.3	$V_{IN} = V_{CC}$ or GND			±0.05		±0.2	μА

Electrical characteristics AS21P2TLR

Table 6. DC specifications (continued)

Symbol				Value					
	Parameter	V _{CC} (V)	Test condition	T _A :	T _A = 25 °C -40 to 85 °			5 °C	Unit
				Min	Тур	Max	Min	Max	
		4.3	V _{1IN,} V _{2IN} = 1.65 V		±37	±50		±100	
I _{CCLV}	Quiescent supply current low voltage driving		V _{1IN,} V _{2IN} = 1.80 V		±33	±40		±50	μА
	3		V _{1IN,} V _{2IN} = 2.60 V		±12	±20		±30	

^{1.} Guaranteed by design.

Table 7. AC electrical characteristics (C $_L$ = 35 pF, R $_L$ = 50 $\Omega,\,t_r$ = $t_f\,\leq\,$ 6 ns)

						Value			
Symbol	Parameter	V _{CC} (V) Test condition	T _A	T _A = 25 °C			-40 to 85 °C		
				Min	Тур	Max	Min	Max	
		1.65 – 1.95			0.45				
t _{PLH,}	Propagation delay	2.3 – 2.7			0.40				ns
t _{PHL}		3.0 - 3.3			0.30				
		3.6 – 4.3			0.30				
		1.65 – 1.95	V _S = 0.8 V		120				
t _{ON}	Turn-ON time	2.3 – 2.7	V _S = 1.5 V		65	85		90	ns
		3.0 – 3.3			42	55		65	
		3.6 - 4.3			40	55		65	
		1.65 – 1.95	V _S = 0.8 V		45				
t _{OFF}	Turn-OFF time	2.3 – 2.7			18	30		40	ns
		3.0 – 3.3	V _S = 1.5 V		16	30		40	
		3.6 - 4.3			15	30		40	
		1.65 – 1.95	- C _L = 35 pF	2	80				
t _D	Break-before make time delay	2.3 – 2.7	$R_L = 50 \Omega$	2	60				ns
	uciay	3.0 – 3.3	V _S = 1.5 V	2	55				
		3.6 - 4.3		2	50				

^{2.} $\Delta R_{ON} = R_{ON(max)} - R_{ON(min)}$.

^{3.} Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

Table 7. AC electrical characteristics (C $_{L}$ = 35 pF, R $_{L}$ = 50 $\Omega,\,t_{r}$ = $t_{f}\,\leq\,$ 6 ns) (continued)

				Value					
Symbol	Parameter	V _{CC} (V)	C (V) Test condition		T _A = 25 °C		-40 to 85 °C		Unit
				Min	Тур	Max	Min	Max	
		1.65 – 1.95	C _L = 100 pF		43				
Q	Charge injection		$R_L = 1 M\Omega$		51				рС
		3.0 – 3.3	$V_{GEN} = 0 V$ $R_{GEN} = 0 \Omega$		51				
		3.6 – 4.3	GLIV 7		49				

Table 8. Analog switch characteristics (C_L = 5 pF, R_L = 50 Ω , T_A = 25 °C)

						Value			
Symbol	Parameter	V _{CC} (V)	Test condition	T _A :	= 25 °C	;	-40 to 8	35 °C	Unit
				Min	Тур	Max	Min	Max	
OIRR	Off isolation ⁽¹⁾	1.65 – 4.3	V _S = 1 V _{RMS} f = 100 kHz		-66				dB
Xtalk	Crosstalk	1.65 – 4.3	$V_S = 1 V_{RMS}$ f = 100 kHz		-72				dB
THD	Total harmonic distortion	2.3 – 4.3	$R_{L} = 600 \Omega$ $V_{IN} = 2V_{PP}$ $f = 20 \text{ Hz to}$ 20 kHz		0.02				%
BW	-3 dB bandwidth	1.65 – 4.3	R _L = 50 Ω		55				MHz
C _{IN}	Control pin input capacitance				5				
C _{Sn}	Sn port capacitance	3.3	f = 1 MHz		40				pF
C _D	D port capacitance when switch is enabled	3.3	f = 1 MHz		114				

^{1.} Off Isolation = 20 \log_{10} (V_D/V_S), V_D = output. V_S = input at off switch.

Test circuit AS21P2TLR

5 Test circuit

Figure 3. ON resistance

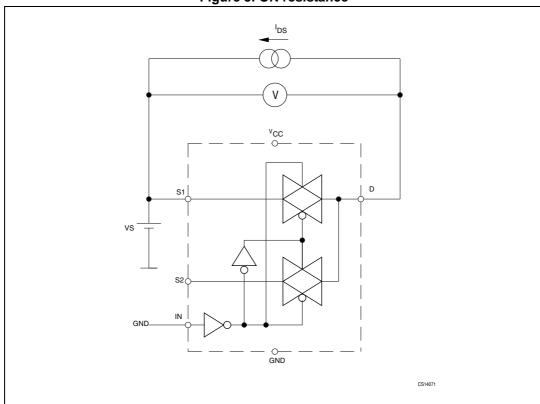
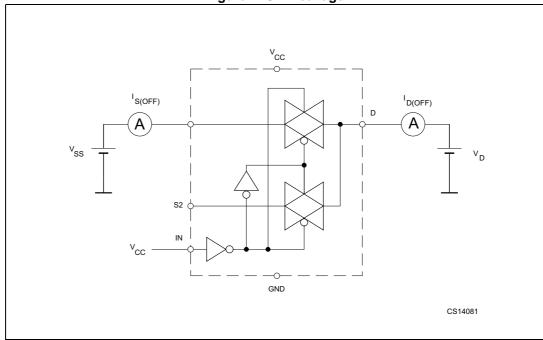


Figure 4. OFF leakage



AS21P2TLR Test circuit

Figure 5. OFF isolation

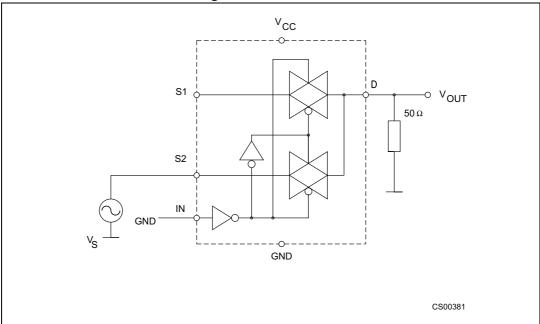
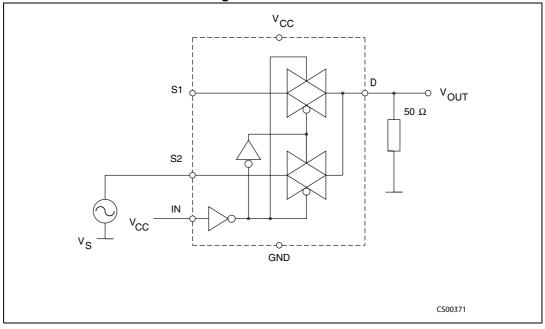


Figure 6. Bandwidth

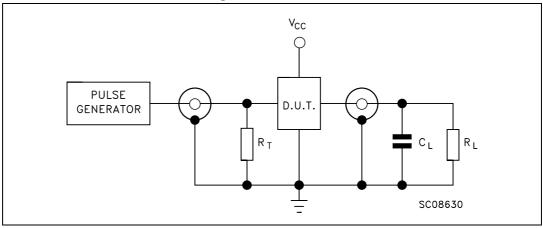


Test circuit AS21P2TLR

 V_{CC} S1 D V_{OUT} \circ $50\;\Omega$ S2 GND CS14091V2

Figure 7. Channel-to-channel crosstalk





^{1.} C_L = 5/35 pF or equivalent (includes jig and probe capacitance). R_L = 50 Ω or equivalent. R_T = Z_{OUT} of pulse generator (typically 50 Ω).

AS21P2TLR Test circuit

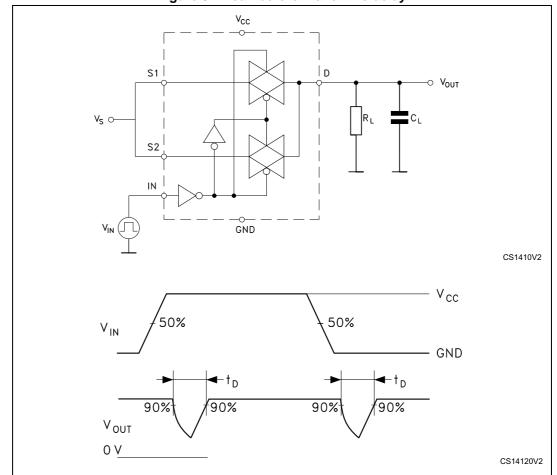


Figure 9. Break-before-make time delay

Test circuit AS21P2TLR

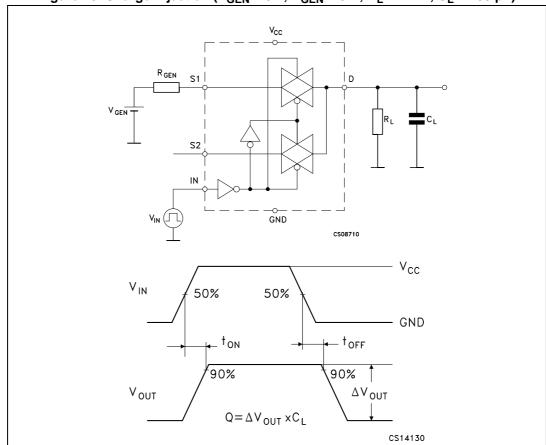


Figure 10. Charge injection (V_{GEN} = 0 V, R_{GEN} = 0 Ω , R_L = 1 M Ω , C_L = 100 pF)

AS21P2TLR Test circuit

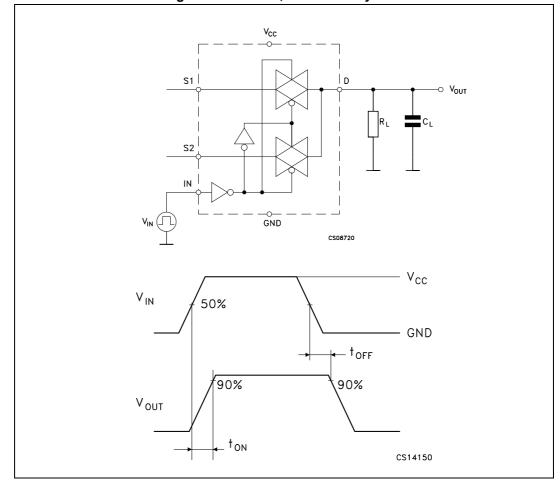


Figure 11. Turn-on, turn-off delay time

6 Package mechanical data

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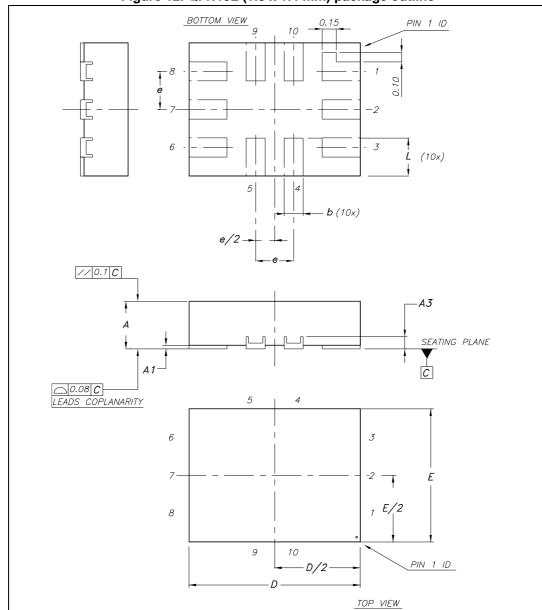
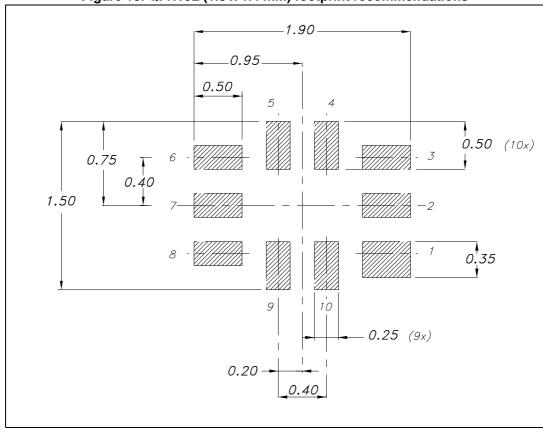


Figure 12. QFN10L (1.8 x 1.4 mm) package outline

Table 9. QFN10L (1.8 x 1.4 mm) mechanical data

Symbol		millimeters			inches	
Symbol	Nom	Min	Max	Nom	Min	Max
А	0.50	0.45	0.55	0.020	0.017	0.021
A1	0.02	0	0.05	0.001	0	0.002
A3	0.127			0.005	0	0
b	0.20	0.15	0.25	0.007	0.006	0.010
D	1.80	1.70	1.90	0.070	0.066	0.074
Е	1.40	1.30	1.50	0.055	0.051	0.059
е	0.40			0.015		
L	0.40	0.30	0.50	0.015	0.011	0.020

Figure 13. QFN10L (1.8 x 1.4 mm) footprint recommendations



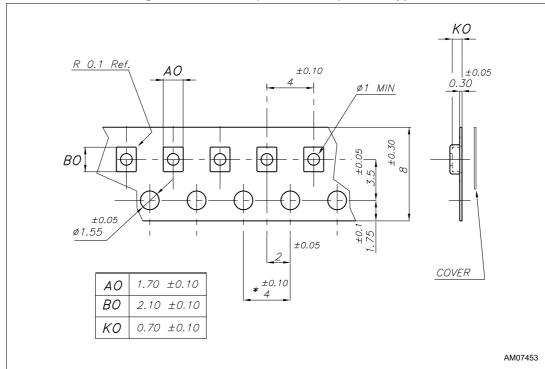


Figure 14. QFN10L (1.8 x 1.4 mm) carrier type

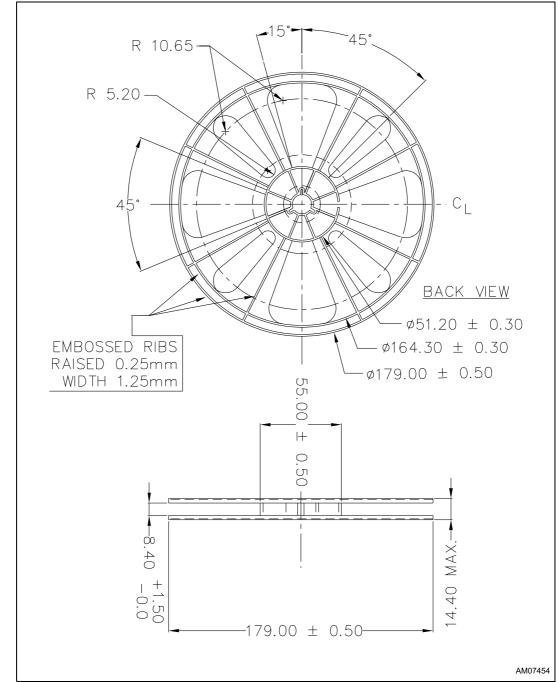


Figure 15. QFN10L (1.8 x 1.4 mm) reel information - back view

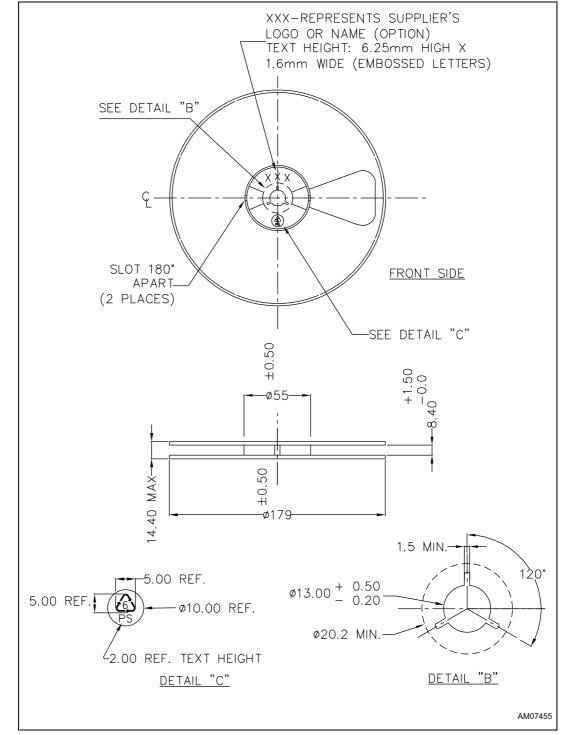


Figure 16. QFN10L (1.8 x 1.4 mm) reel information - front side



AS21P2TLR Revision history

7 Revision history

Table 10. Document revision history

Date	Revision	Changes
07-Mar-2014	1	Initial release.

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